High-speed switching diodes Rev. 8 — 18 November 2010

Product data sheet

1. **Product profile**

1.1 General description

High-speed switching diodes, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

| Type number | Package | | | Configuration | Package |
|-------------|---------|-------|----------|---------------------|---------------|
| | NXP | JEITA | JEDEC | | configuration |
| BAV99 | SOT23 | - | TO-236AB | dual series | small |
| BAV99S | SOT363 | SC-88 | - | quadruple; 2 series | very small |
| BAV99W | SOT323 | SC-70 | - | dual series | very small |

1.2 Features and benefits

- High switching speed: $t_{rr} \le 4$ ns
- Low leakage current
- Small SMD plastic packages

1.3 Applications

- High-speed switching
- General-purpose switching

1.4 Quick reference data

- Low capacitance: C_d ≤ 1.5 pF
- Reverse voltage: $V_R \le 100 \text{ V}$
- AEC-Q101 qualified
- Reverse polarity protection

| Quick reference data | | | | | |
|-----------------------|---|--|--|--|---|
| Parameter | Conditions | Min | Тур | Max | Unit |
|) | | | | | |
| reverse current | V _R = 80 V | - | - | 0.5 | μA |
| reverse voltage | | - | - | 100 | V |
| reverse recovery time | | <u>[1]</u> - | - | 4 | ns |
| | Parameter reverse current reverse voltage | Parameter Conditions reverse current V _R = 80 V reverse voltage | Parameter Conditions Min reverse current V _R = 80 V - reverse voltage - - | Parameter Conditions Min Typ reverse current V _R = 80 V - - reverse voltage - - - | ParameterConditionsMinTypMaxreverse currentVR = 80 V0.5reverse voltage100 |

[1] When switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA.



High-speed switching diodes

2. Pinning information

| Pin | Description | Simplified outline | Graphic symbol |
|----------|---------------------------------------|----------------------------------|------------------|
| BAV99; I | BAV99W | | |
| 1 | anode (diode 1) | | |
| 2 | cathode (diode 2) | 3 | 3 |
| 3 | cathode (diode 1), anode (diode 2) | 1 2 006aaa144 | 1 2 006aaa763 |
| BAV99S | | | |
| 1 | anode (diode 1) | D - D - D - | |
| 2 | cathode (diode 2) | | 6 5 4 |
| 3 | cathode (diode 3), anode (diode 4) | 0 | |
| 4 | anode (diode 3) | | |
| 5 | cathode (diode 4) | | 1 2 3 |
| 6 | cathode (diode 1), anode (diode 2) | | 006aab101 |

3. Ordering information

| Table 4. Orde | ering inforn | nation | |
|---------------|--------------|--|---------|
| Type number | Package | | |
| | Name | Description | Version |
| BAV99 | - | plastic surface-mounted package; 3 leads | SOT23 |
| BAV99S | SC-88 | plastic surface-mounted package; 6 leads | SOT363 |
| BAV99W | SC-70 | plastic surface-mounted package; 3 leads | SOT323 |
| | | | |

4. Marking

| Table 5. Marking codes Type number | Marking code ^[1] |
|------------------------------------|-----------------------------|
| BAV99 | A7* |
| BAV99S | K1* |
| BAV99W | A7* |

[1] * = placeholder for manufacturing site code

BAV99_SER Product data sheet

High-speed switching diodes

5. Limiting values

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|--|------------------------------|--------------|------|------|
| Per diode | | | | | |
| V _{RRM} | repetitive peak reverse voltage | | - | 100 | V |
| V _R | reverse voltage | | - | 100 | V |
| I _F | forward current | | | | |
| | BAV99 | | [1] - | 215 | mA |
| | | | [2] _ | 125 | mA |
| | BAV99S | | <u>[1]</u> _ | 200 | mA |
| | BAV99W | | <u>[1]</u> - | 150 | mA |
| | | | [2] _ | 130 | mA |
| I _{FRM} | repetitive peak forward current | | - | 500 | mA |
| I _{FSM} | non-repetitive peak forward current | square wave | [3] | | |
| | | t _p = 1 μs | - | 4 | А |
| | | t _p = 1 ms | - | 1 | А |
| | | t _p = 1 s | - | 0.5 | А |
| P _{tot} | total power dissipation | | [1][4] | | |
| | BAV99 | $T_{amb} \le 25 \ ^{\circ}C$ | - | 250 | mW |
| | BAV99S | $T_{sp} \le 85 \ ^{\circ}C$ | [5] _ | 250 | mW |
| | BAV99W | $T_{amb} \le 25 \ ^{\circ}C$ | - | 200 | mW |
| Per device | | | | | |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -65 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |

[1] Single diode loaded.

[2] Double diode loaded.

[3] $T_j = 25 \ ^\circ C$ prior to surge.

[4] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[5] Soldering points at pins 2, 3, 5 and 6.

High-speed switching diodes

6. Thermal characteristics

| Table 7. | Thermal characteristics | | | | | |
|-----------------------|---|-------------|---------------|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | <u>[1][2]</u> | | | |
| | BAV99 | | - | - | 500 | K/W |
| | BAV99W | | - | - | 625 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | | | |
| | BAV99 | | - | - | 360 | K/W |
| | BAV99S | | [3] _ | - | 260 | K/W |
| | BAV99W | | - | - | 300 | K/W |
| | | | | | | |

[1] Single diode loaded.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Soldering points at pins 2, 3, 5 and 6.

7. Characteristics

Table 8.Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

| anno — - | | | | | | |
|-----------------|--------------------------------|--|--------------|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Per diode |) | | | | | |
| V _F | / _F forward voltage | I _F = 1 mA | - | - | 715 | mV |
| | I _F = 10 mA | - | - | 855 | mV | |
| | | I _F = 50 mA | - | - | 1 | V |
| | | I _F = 150 mA | - | - | 1.25 | V |
| I _R | I _R reverse current | V _R = 25 V | - | - | 30 | nA |
| | | V _R = 80 V | - | - | 0.5 | μΑ |
| | | $V_{R} = 25 \text{ V}; \text{ T}_{j} = 150 ^{\circ}\text{C}$ | - | - | 30 | μΑ |
| | | $V_{R} = 80 \text{ V}; \text{ T}_{j} = 150 ^{\circ}\text{C}$ | - | - | 50 | μΑ |
| C _d | diode capacitance | $f = 1 MHz; V_R = 0 V$ | - | - | 1.5 | pF |
| t _{rr} | reverse recovery time | | <u>[1]</u> _ | - | 4 | ns |
| $V_{\sf FR}$ | forward recovery voltage | | [2] _ | - | 1.75 | V |
| | | | | | | |

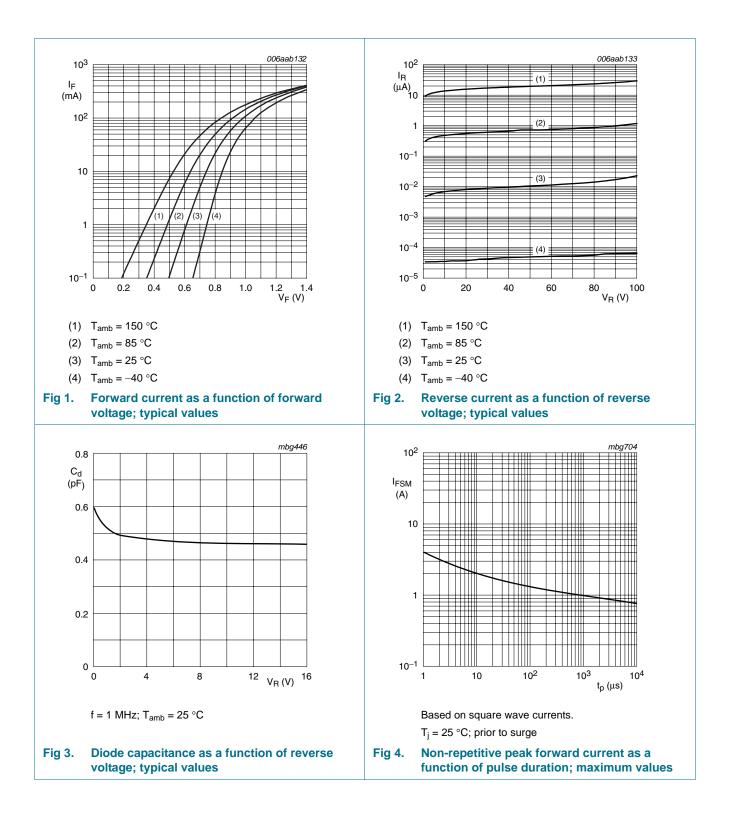
[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

[2] When switched from $I_F = 10$ mA; $t_r = 20$ ns.

NXP Semiconductors

BAV99 series

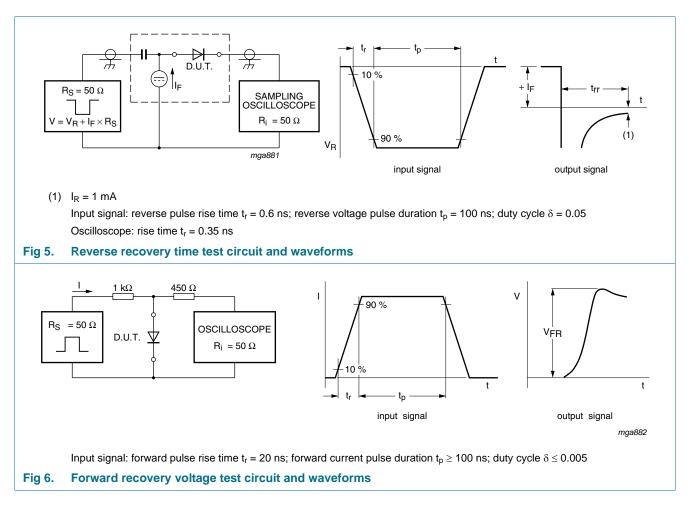
High-speed switching diodes



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8. Test information

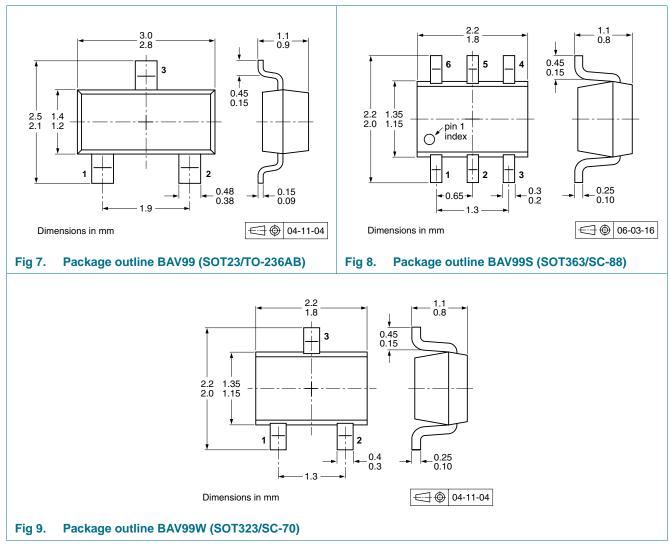


8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

High-speed switching diodes

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description | Packing c | juantity |
|-------------|---------|--|-----------|----------|
| | | | 3000 | 10000 |
| BAV99 | SOT23 | 4 mm pitch, 8 mm tape and reel | -215 | -235 |
| BAV99S | SOT363 | 4 mm pitch, 8 mm tape and reel; T1 [2] | -115 | -135 |
| | | 4 mm pitch, 8 mm tape and reel; T2 [3] | -125 | -165 |
| BAV99W | SOT323 | 4 mm pitch, 8 mm tape and reel | -115 | -135 |

[1] For further information and the availability of packing methods, see Section 14.

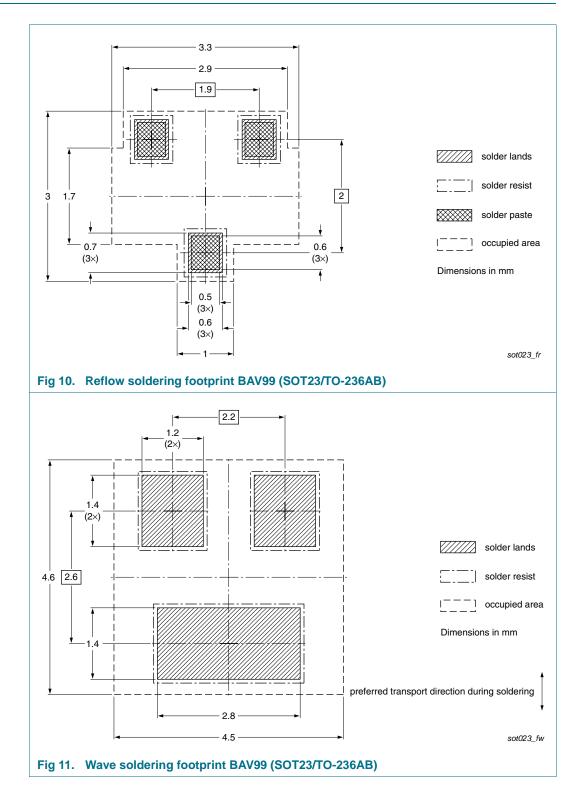
[2] T1: normal taping

[3] T2: reverse taping

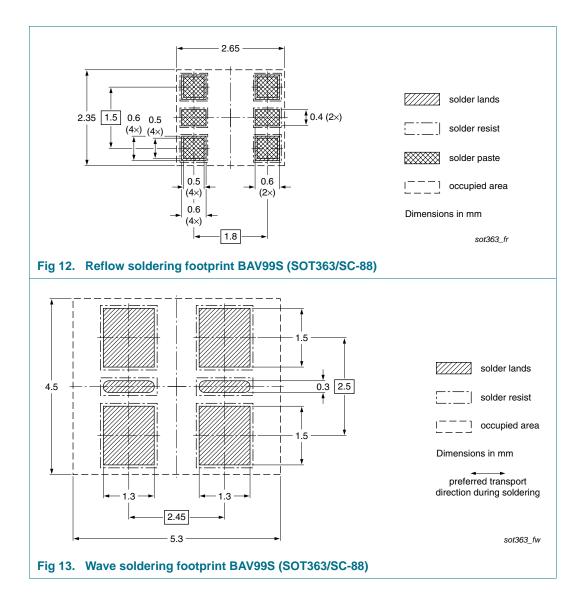
BAV99 SER

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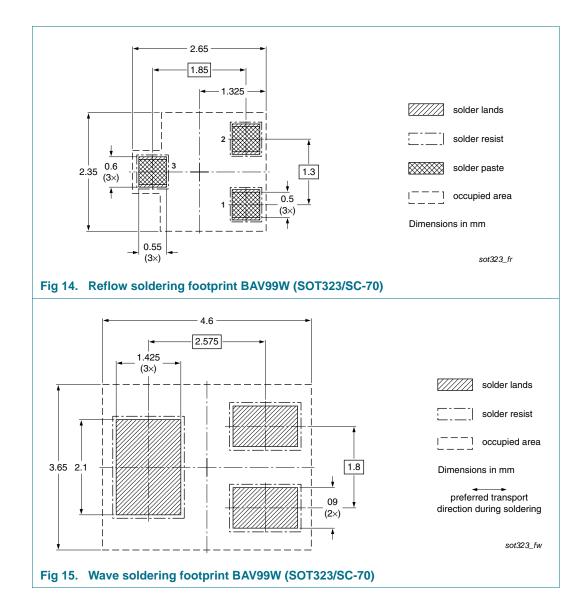
11. Soldering



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High-speed switching diodes

12. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|----------------------------------|--|-------------------------|----------------|
| BAV99_SER_8 | 20101118 | Product data sheet | - | BAV99_SER_7 |
| Modifications: | Section 4 " | Marking": marking placehold | er explanation in table | footer updated |
| | Section 5 "L | <u>_imiting values"</u> : P _{tot} condition | on for BAV99S corrected | d |
| | Section 13 | "Legal information": updated | 1 | |
| BAV99_SER_7 | 20100414 | Product data sheet | - | BAV99_SER_6 |
| BAV99_SER_6 | 20100310 | Product data sheet | - | BAV99_SER_5 |
| BAV99_SER_5 | 20080820 | Product data sheet | - | BAV99_4 |
| | | | | BAV99S_3 |
| | | | | BAV99W_4 |
| BAV99_4 | 20011015 | Product specification | - | BAV99_3 |
| BAV99S_3 | 20010514 | Product specification | - | BAV99S_N_2 |
| BAV99W 4 | 19990511 | Product specification | - | BAV99W 3 |

13. Legal information

13.1 Data sheet status

| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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